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Type	L #	Hits	Search Text	DBS	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	720 LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55			0
2	BRS	L2	51 lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55			0
3	BRS	L3	60 lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
4	BRS	L4	479 LDDMOSS2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
5	BRS	L5	74 (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
6	BRS	L6	178 lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
7	BRS	L7	250 lateral\$4 near7 (metal adj oxide adj semiconduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0

Type	L #	Hits	Search Text	DBS	Time Stamp	Comments	Error Definition	Errors
8	BRS	L8	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57		0
9	BRS	L9	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57		0
10	BRS	L10	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57		0
11	BRS	L11	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58		0
12	BRS	L12	8142	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:59		0
13	BRS	L13	9374	1 or 2 or 3 or 4 or 5 or 6 or 7 or 8 or 9 or 10 or 11 or 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:03		0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
14	BRS	L14	43547 (amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44		0	
15	BRS	L15	334 13 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:06		0	
16	BRS	L16	5148 implants\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:13		0	
17	BRS	L17	43678 (silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:09		0	
18	BRS	L22	25985 implants\$8 near8 (silicon or US-PGPUB; Si or "Si" or Ge or "Ge" or EPO; JPO; germanium) DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:22		0	
19	BRS	L23	7645 implants\$8 with 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:24		0	
20	BRS	L24	26134 16 or 22 or 23	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25		0	

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21	BRS	L25	176	24 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25		0
22	BRS	L26	152356	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:36		0
23	BRS	L27	141012	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STRI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:37		0
24	BRS	L28	120	25 and 27	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38		0
25	BRS	L29	109	26 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38		0
26	BRS	L30	1255	24 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44		0
27	BRS	L31	280	30 and (amorphous or amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:45		0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
28	BRS	L32	172	26 and 27 and 31	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:46		0
29	BRS	L33	280	25 or 31	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:54		0
30	BRS	L34	848	24 with (amorphous or amorphs9) with (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:57		0
31	BRS	L35	45	34 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:57		0
32	BRS	L36	1853	24 same (amorphous or amorphs9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:58		0
33	BRS	L37	78	36 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:58		0
34	BRS	L38	43237	(crystall1\$9 or re-crystall1\$9 or (re adj crystall1\$9)) with amorphs9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:53		0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
35	BRS	L39	8629 gaussian with (distribut\$6 or profil\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:55			0
36	BRS	L40	3 35 and 38 and 39	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:56			0
37	BRS	L41	3 37 and 38 and 39	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:56			0
38	BRS	L42	6 33 and 38 and 39	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:58			0
39	BRS	L43	25 35 and 38	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:59			0
40	BRS	L44	35 37 and 38	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:59			0

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2	BRS	L2	51 lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55			0
3	BRS	L3	60 lateral\$4 adj diffus\$5 adj (MOSS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
4	BRS	L4	479 LDDMOS\$2 or LDD-MOSS\$2 or (LDD adj MOSS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
5	BRS	L5	74 (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
6	BRS	L6	178 lateral\$4 adj double adj diffus\$5 adj (MOSS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
7	BRS	L7	250 lateral\$4 near7 (metal adj oxide adj semiconduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0

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8	BRS	L8	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57		0
9	BRS	L9	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57		0
10	BRS	L10	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57		0
11	BRS	L11	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58		0
12	BRS	L12	8142	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:59		0
13	BRS	L13	9374	1 or 2 or 3 or 4 or 5 or 6 or 7 or 8 or 9 or 10 or 11 or 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:03		0

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14	BRS	L14	43547 (amorphous or amorphous) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44			0
15	BRS	L15	334 13 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:06			0
16	BRS	L16	5148 implants\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:13			0
17	BRS	L17	43678 (silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:09			0
18	BRS	L22	25985 implants\$8 near8 (silicon or US-PGPUB; Si or "Si" or Ge or "Ge" or EPO; JPO; germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:22			0
19	BRS	L23	7645 implants\$8 with 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:24			0
20	BRS	L24	26134 16 or 22 or 23	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25			0

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22	BRS	L26	152356	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:36		0
23	BRS	L27	141012	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:37		0
24	BRS	L28	120	25 and 27	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38		0
25	BRS	L29	109	26 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38		0
26	BRS	L30	1255	24 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44		0
27	BRS	L31	280	30 and (amorphous or amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:45		0

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29	BRS	L33	280	25 or 31	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:54		0
30	BRS	L34	848	24 with (amorphous or amorph\$9) with (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:57		0
31	BRS	L35	45	34 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:57		0
32	BRS	L36	1853	24 same (amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:58		0
33	BRS	L37	78	36 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:58		0

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2	BRS	L2	51	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55		0
3	BRS	L3	60	lateral\$4 adj diffus\$5 adj (MOSS\$3 or MOSFET\$1)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56		0
4	BRS	L4	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOSS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56		0
5	BRS	L5	74	(lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56		0
6	BRS	L6	178	lateral\$4 adj double adj diffus\$5 adj (MOSS\$3 or MOSFET\$1)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56		0
7	BRS	L7	250	lateral\$4 near7 (metal adj oxide adj semiconduct\$4)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57		0

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9	BRS	L9	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57		0
10	BRS	L10	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57		0
11	BRS	L11	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58		0
12	BRS	L12	8142	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistors\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:59		0
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15	BRS	L15	334 13 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:06		0	
16	BRS	L16	5148 implants\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:13		0	
17	BRS	L17	43678 (silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:09		0	
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27	BRS	L31	280 30 and (amorphous or amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:45			0

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7	BRS	L7	250 lateral\$4 near7 (metal adj oxide adj semiconduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
8	BRS	L8	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
9	BRS	L9	LDP MOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
10	BRS	L10	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
11	BRS	L11	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58			0
12	BRS	L12	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:59			0
13	BRS	L13	1 or 2 or 3 or 4 or 5 or 6 or 7 or 8 or 9 or 10 or 11 or 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:03			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
14	BRS	L14	43547 (amorphous or amorphous) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:05		0	
15	BRS	L15	334 13 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:06		0	
16	BRS	L16	5148 implants\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:13		0	
17	BRS	L17	43678 (silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:09		0	
18	BRS	L22	25985 implants\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:22		0	
19	BRS	L23	7645 implants\$8 with 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:24		0	
20	BRS	L24	26134 16 or 22 or 23	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25		0	

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Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
21	BRS	L25	176	24 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25		0
22	BRS	L26	152356	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:36		0
23	BRS	L27	141012	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:37		0
24	BRS	L28	120	25 and 27	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38		0
25	BRS	L29	109	26 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38		0